

**1. Scope :**

This specification applies to P/N silicon zener diode chips,  
Device NO. SD-30614G

**2. Structure :**

- 2-1. Planar type : P/N Diode
- 2-2. Electrodes :  
Top side : Gold pad.  
Back side : Gold layer.

**3. Size :**

- 3-1. <sup>\*\*1</sup> Chip size : 6.88 mils x 6.88 mils (0.175 mm x 0.175 mm ).
- 3-2. Chip thickness :  $3.3 \pm 0.6$  mils ( $0.085 \pm 0.015$  mm )
- 3-3. Active area : 4.1 mils x 4.1 mils (0.105 mm x 0.105 mm).
- 3-4. Bonding pad : 4.8 mils x 4.8 mils (0.122 mm x 0.122 mm).
- 3-5. Pattern drawing : Refer to the attached drawing.  
<sup>\*\*1</sup>Including scribing line. The chip size is about  $(0.150 \pm 0.015)^2$ mm<sup>2</sup> after dicing.

**4. Electrical characteristics (Ta = 25 °C)**

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Reverse Leakage Current	I <sub>R</sub>	V <sub>R</sub> =11V E <sub>e</sub> =0mW/cm <sup>2</sup>			100	nA
Zener Voltage	V <sub>Z</sub>	I <sub>Z</sub> =5mA E <sub>e</sub> =0mW/cm <sup>2</sup>	12.5	14.0	15.5	V
Forward Voltage	V <sub>f</sub>	I <sub>F</sub> =20mA E <sub>e</sub> =0mW/cm <sup>2</sup>	0.75		1.2	V

